

Large Current External FET Switching Regulator Controllers

High Efficiency Step-down Switching Regulator Controller

BD9775FV No.11028EAT17

Description

BD9775FV is Switching Controller with synchronous rectification (BD9775FV is 1channel synchronous rectification) and wide input range. It can contribute to ecological design (lower power consumption) for most of electronic equipments.

Features

- 1) 2channel Step-Down DC/DC FET driver
- 2) Synchronous rectification for channel 2
- 3) Able to synchronize to an external clock signal
- 4) Over Current Protection (OCP) by monitoring VDS of P channel FET
- 5) Short Circuit Protection (SCP) by delay time and latch method
- 6) Under Voltage Lock Out (UVLO)
- 7) Thermal Shut Down (TSD)
- 8) Package: SSOP-B28

Applications

Car navigation system, Car Audio, Display, Flat TV

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Supply Voltage (VCC to GND)	VCC	36	V
VREF to GND Voltage	Vref	7	V
VREGA to GND Voltage	Vrega	7	V
VREGB to VCC Voltage	Vregb	7	V
OUT1, OUT2H to VCC Voltage	Vouth	7	V
OUT2L to GND Voltage	Voutl	7	V
Power Dissipation	Pd	640 ^(*1)	mW
Operating Temperature Range	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +125	°C
Junction Temperature	Tjmax	+125	°C

^(*1) Without heat sink, reduce to 6.4mW when Ta=25°C or above

Pd is 850mW mounted on 70x70x1.6mm, and reduce to 8.5mW/°C above 25°C.

● Recommended operating conditions (Ta=-25 to +75°C)

Parameter	Symbol		Unit		
Farameter	Symbol	Min.	Тур.	Typ. Max.	
Supply Voltage	VCC	6.0	-	30.0	V
Oscillating Frequency	fosc	30	100	300	kHz
Timing Resistance	RT	10	27	56	kΩ
Timing Capacitance	СТ	100	470	4700	pF

● Electrical characteristics (Ta=25°C, VCC=13.2V, fosc=100kHz, CTL1=3V, CTL2=3V)

ctrical characteristics (Ta=25°C, VCC=13.2V, fosc=100kHz, CTL1=3V, CTL2=3V) Limits						
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
[Whole Device]			<u> </u>			
Stand-by Current	Iccst	_	_	5	μA	CTL1,CTL2=0V
Circuit Current	Icc	2.5	4.2	7	mA	FB1,FB2=0V
[Reference Voltage]						
VREF Output Voltage	Vref	2.97	3.00	3.03	V	Io=-1mA
Line Regulation	DVIi	_	_	10	mV	Vcc=7 to 18V,lo=-1mA
Load Regulation	DVlo	_	_	10	mV	lo=-0.1mA to -2mA
Short Output Current	los	-60	-22	-5	mA	
[Internal Voltage Regulator]						
VREGA Output Voltage	Vrega	4.5	5.0	5.5	V	Switching with COUT=5000pF
VREGB Output Voltage	Vregb	VCC-5.5	VCC-5.0	VCC-4.5	V	Switching with COUT=5000pF
VREGB Dropout Voltage	Vdregb	_	1.8	2.2	>	VREGB to GND Voltage
[Oscillator]						
Oscillating Frequency	fosc	90	100	110	kHz	RT=27kΩ,CT=470pF
Frequency Tolerance	Dfosc	_	_	2	%	Vcc=7 to 18V
[Synchronized Frequency]						
Synchronized Frequency	fosc2	_	120	_	kHz	FIN=120kHz
FIN Threshold Voltage	Vthfin	1.2	1.4	1.6	V	
FIN Input Current	IFIN	-1	_	1	μΑ	VFIN=1.4V
[Error Amplifier]						
Threshold Voltage	Vthea	0.98	1.00	1.02	V	
INV Input Bias Current	Ibias	-1	_	1	μΑ	
Voltage Gain	Av	_	70	_	dB	DC
Band Width	Bw	_	2.0	_	MHz	Av=0dB
Maximum Output Voltage	Vfbh	2.2	2.4	2.6	٧	INV=0.5V
Minimum Output Voltage	VfbI	_	_	0.1	٧	INV=1.5V
Output Sink Current	Isink	0.5	2	5.2	mA	FB1,2 Terminal
Output Source Current	Isource1	-170	-110	-70	μA	FB1 Terminal
2 Sipar Course Carron	Isource2	-200	-130	-85	μΑ	FB2 Terminal

Parameter Symbol Limits		Unit		Condition		
	Суппоот	Min.	Тур.	Max.	Jill	Condition
[PWM Comparator]	T	T	T	Т		T
Threshold Voltage at 0%	Vth0	0.88	0.98	1.08	V	FB Voltage
Threshold Voltage at 100%	Vth100	1.88	1.98	2.08	V	FB Voltage
DTC Input Bias Current	Idtc	-1	_	1	μΑ	
[FET Driver]						
Sink Current	Isink	20	36	58	mA	VDS=0.4V
Source Current	Isource	-510	-320	-180	mA	VDS=0.4V
ON Resistance	RonN	7.0	11.0	17.8	Ω	OUT1,2H,2L : L
OTT TOSIStation	RonP	0.7	1.4	2.2	Ω	OUT1,2H,2L : H
Rise Time	Tr	_	20	_	nsec	Switching with COUT=5000pF
Fall Time	Tf	_	100	_	nsec	Switching with COUT=5000pF
Driver's Duty Cycle of Synchronous Rectification	Δ Duty	42	45	48	%	$\begin{array}{c} \text{RSYNC=30K}\Omega,\\ \text{50\% of main driver's duty cycle} \end{array}$
SYNC Terminal Voltage	Vsync	1.45	1.55	1.65	V	Rsync=30K Ω ,FB=1.5V
[Over Current Protection (OCP)]						
VS Threshold Voltage	Vths	VCC-0.24	VCC-0.21	VCC-0.18	V	RCL=21k Ω , the output turn off after detected 8 cycle
VS Input Current	IVSH	-1	_	1	μA	VS1,VS2=PBU
	IVSL	-1	_	1	μA	VS1,VS2=0V
CL Input Current	Icl	9	10	11	μΑ	
[Stand-by]		1		1		Т
Threshold Voltage	Vctl	1.0	1.5	2.0	V	
CL Input Current	Ictl	6	15	30	μA	CTL1,CTL2=3V
[Short Circuit Protection (SCP)]						
Timer Start Voltage	Vtime	0.6	0.7	0.8	V	INV Voltage
Threshold Voltage	Vthscp	1.92	2.00	2.08	V	SCP Voltage
Stand-by Voltage	Vstscp	_	10	100	mV	SCP Voltage
Source current	Isoscp	-4.0	-2.5	-1.5	μA	SCP=1.0V
[Under Voltage Lock Out (UVLO)]						
Threshold Voltage	Vuvlo	5.6	5.7	5.8	V	Vcc sweep down
Hysteresis Voltage Range	DVuvlo	0.05	0.1	0.15	V	
		1				i e

●Pin Description

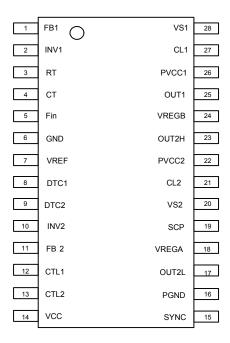


Fig.1 Pin Description

Block Diagram

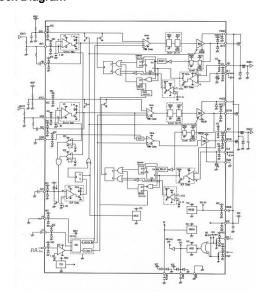


Fig.2 Block Diagram

●Pin No. / Pin Name

Pin No.	Pin Na Pin Name	Description
1	FB1	Error amplifier output pin(Channel 1)
2	INV1	Error amplifier negative input pin(Channel 1)
3	RT	Oscillator frequency adjustment pin
		connected resistor Oscillator frequency adjustment pin
4	СТ	connected capacitor
5	FIN	Oscillator synchronization pulse signal input pin
6	GND	Low-noise ground
7	VREF	Reference voltage output pin
8	DTC1	Maximum duty and soft start adjustment pin (Channel 1)
9	DTC2	Maximum duty and soft start adjustment pin (Channel 2)
10	INV2	Error amplifier negative input pin(Channel 2)
11	FB2	Error amplifier output pin(Channel 2)
12	CTL1	Enable/stand-by control input(Channel 1)
13	CTL2	Enable/stand-by control input(Channel 2)
14	VCC	Main power supply pin
15	SYNC	Synchronous rectification timing adjustable pin
16	PGND	Power ground (connected low-side gate driver and digital ground)
17	OUT2L	Low-side (synchronous rectifier) gate driver output pin(Channel 2)
18	VREGA	Connected capacitor for internal regulator
19	SCP	Delay time of short circuit protection adjustment pin connected capacitor
20	VS2	Over current detection voltage monitor pin (connected FET drain, Channel 2)
21	CL2	Over current detection voltage adjustment pin connected capacitor and resistor(Channel 2)
22	PVCC2	High-side gate driver power supply input (Channel 2)
23	OUT2H	High-side gate driver output pin(Channel 2)
24	VREGB	Connected capacitor for internal regulator
25	OUT1	High-side gate driver output pin(Channel 1)
26	PVCC1	High-side gate driver power supply input (Channel 1)
27	CL1	Over current detection voltage adjustment pin connected capacitor and resistor(Channel 1)
28	VS1	Over current detection voltage monitor pin (connected FET drain, Channel 1)

●Function Explanation

1. DC/DC Converter

· Reference Voltage

Stable voltage of compensated temperature, is generated from the power supply voltage (VCC). The reference voltage is 3.0V, the accuracy is $\pm 1\%$. Place a capacitor with low ESR (several decades m Ω) between VREF and GND.

Internal Regulator A (VREGA)

5V is generated the power supply voltage. The voltage is for the driver of the synchronous rectification's MOSFET. Place a capacitor with low ESR (several decades $m\Omega$) between VREGA and PGND.

Internal regulator B (VREGB)

(VCC-5V) is generated from the power supply voltage. The voltage is for the driver of the main MOSFET switch. Place a capacitor with low ESR (several decades $m\Omega$) between VREGB and PVCC.

Oscillator

Placing a resistor and a capacitor to RT and CT, respectively, generates two triangle waves for both cannels, and each wave is opposite phase. The waves are input to the PWM comparators for CH1 and CH2. Also, the oscillating frequency can be slightly adjusted (less than 20%) by putting external clock pulse into Fin pin, which is higher frequency than the fixed one.

Error Amplifier

It amplifies the difference, between the establish output voltage and the actual output one detected at INV. And amplified voltage comes out from FB. The comparing voltage is 1.0V and the accuracy is $\pm 2\%$. The phase can be compensated externally by placing a resistor and a capacitor between INV and FB.

PWM Comparator

It converts the output voltage from error amplifier into PWM waveform, then output to MOSFET driver.

MOSFET Driver

The main drivers (OUT1, OUT2H) are for P-channel MOSFETs, and the driver (OUT2L) for synchronous rectification is for N-channel MOSFET. The values of output voltage are clamp to VREGB, VREGA, respectively. All drivers' output configurations are push-pull type. In addition, the output current capability is 36mA for the sink current and 320mA (Vds=0.4V) for the source current.

2. Channel Control

Each output can be individually turned on or off with CTL1 and CTL2. When the CTL is "H" (more than 1.5V), it becomes turned on.

3. Protection

Over Current Protection(OCP)

When detected over current (detecting drop voltage of the main MOSFET's ON resistance), the MOSFET switch becomes turned off, and the energy on DTC pin is discharged. After discharged, the output restarts automatically. The level of the OCP detection threshold can be set by the resistance, which is connected between VCC and CL.

Short Circuit Protection(SCP)

When either output goes down and the voltage on INV pin gets lower than 0.7V, a capacitor placed on SCP is started to charge.

When the SCP pin becomes more than 2.0V, the main MOSFET switches of both outputs are turned off; then, the outputs are latched. While they are latched, the IC can be reset by restarting VCC or CTL, or discharging SCP.

Under Voltage Lock Out(UVLO)

Due to avoiding malfunctions when the IC is started up or the power supply voltage is rapidly disconnected, the main MOSFET switches become off and DTC is discharged when the supply voltage is less than 5.7V. Also, when the output is latched because of SCP function, the latch becomes reset. Due to preventing malfunctions in the case the power supply voltage fluctuate at near UVLO threshold, there is 0.1V hysteresis between the detection and reset voltage of UVLO threshold.

Thermal Shut Down(TSD)

Due to preventing breakdown of the IC by heating up, the main MOSFET switches become off and DTC pin is discharged by detecting over temperature of the chip. Due to preventing malfunctions in the case temperature fluctuate at near TSD threshold, there is hysteresis between TSD on and off.

Setting Up Information

1) Simultaneously OFF Duty of MOSFETs for Synchronous Rectification

The simultaneously OFF duty of both main MOSFET switch and synchronous rectification MOSFET is determined by resistance (Rsync) between SYNC and GND. See Fig.3. In Synchronous Rectification, insert RFB2-GND (RFB2-GND≒3 × Rsync) between FB2 and GND, because it is possible to reduce overshoot(see Fig.3). RFB2-GND decides following formula.

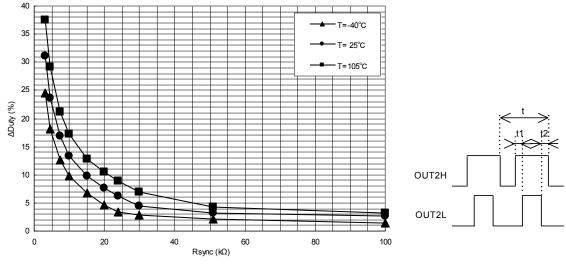


Fig.3

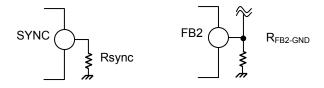
· Resistance at FB2-GND setup condition

$$\frac{\text{Vsync}}{3 \times \text{Rsync}(\text{MAX})} \text{ -Output Source Current at FB2} < R_{\text{FB2-GND}} < 3xRsync(MIN)$$

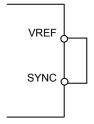
$$\frac{2.08}{0.4908} < R_{\text{FB2-GND}} < 3xRsync(MIN)$$

$$\frac{2.08}{\text{Rsync}(\text{MAX})} + 80.7x10^{-6}$$

**Rsync(MAX)···MAX dispersion range at Rsync Rsync(MIN)···MIN dispersion range at Rsync



Short SYNC to VREF if the synchronous rectification function is not needed.



Without Synchronous Rectification(Don't insert R_{FB2-GND})

2) Oscillator Synchronization by External Pulse Signal

At the operation the oscillator is externally synchronized, input the synchronization signal into Fin in addition to connect a resistor and a capacitor at RT and CT, respectively. Input the external clock pulse on Fin, which is higher frequency than the fixed one. However, the frequency variation should be less than 20%. Also, the duty cycle of the pulse should be set from 10% to 90%.

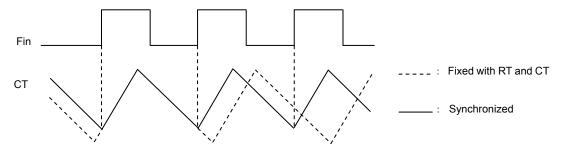


Fig.4 CT Waveform during Synchronized with External Pulse

Short Fin to GND if the function of external synchronization is not needed.

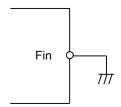


Fig.5 Without Synchronization Signal

3) Setting the Over Current Threshold Level

The \overrightarrow{OCP} detection level (locp) is determined by the ON resistance (R_{ON}) of the main MOSFET switch and the resistance (Rcl) which is placed between CL and VCC.

$$locp = \frac{Rcl}{R_{ON}} \times 10^{-5} [A] (typ.)$$

To prevent a malfunction caused by noise, place a capacitor (Ccl) parallel to Rcl. If OCP function is not needed, short VS to VCC, and short CL to GND.

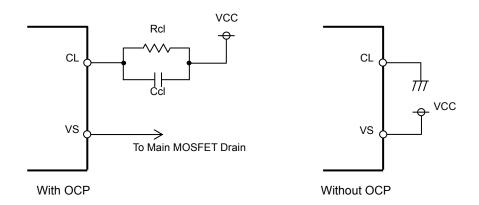


Fig.6 CL, VS Pin Connection

4) Setting the Time for Short Circuit Protection

The time (tscp) from output short to latch activation is determined by the capacitor, Cscp, connected SCP pin.

$$tscp=7.96 \times 10^5 \times Cscp$$
 [sec] (typ.)

Short SCP to GND if SCP function is not being used.

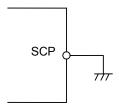
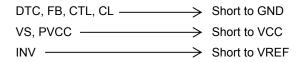


Fig.7 Without SCP

5) Single Channel Operation

This device can be used as a single output. The connection is as follows;



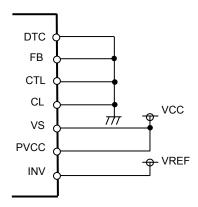
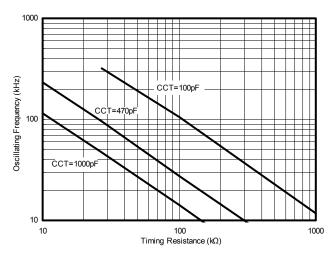
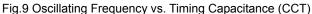


Fig.8 Single Channel Operation

6) Setting the Oscillating Frequency

The oscillating frequency can be set by selecting the timing resistor (RRT) and the timing capacitor (CCT).





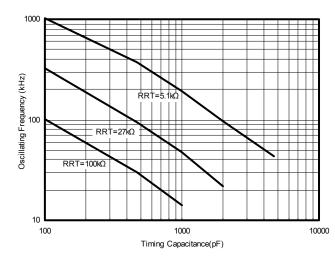


Fig.10 Oscillating Frequency vs. Timing Capacitance (RRT)

●Timing Chart

Output ON/OFF, Minimum Input(UVLO)

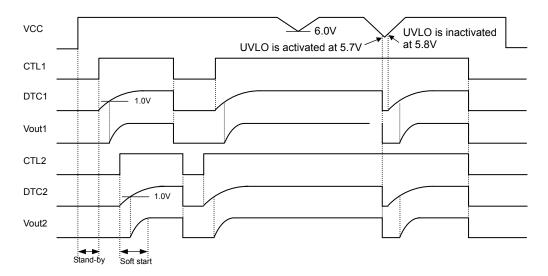


Fig.11

· Over Current Protection, Short Circuit Protection, Thermal Shut Down

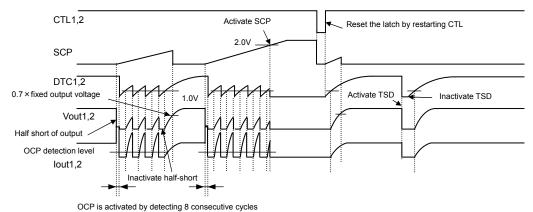


Fig.12

●I/O Equivalent Circuit

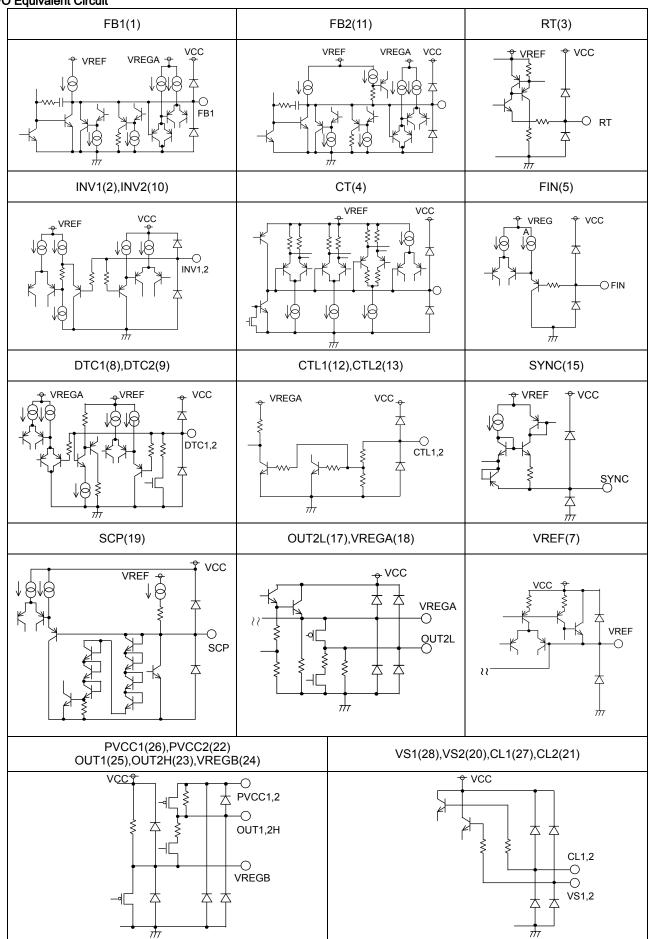


Fig.13

Notes for use

1) Absolute maximum ratings

Use of the IC in excess of absolute maximum ratings such as the applied voltage or operating temperature range may result in IC deterioration or damage. Assumptions should not be made regarding the state of the IC (short mode or open mode) when such damage is suffered. A physical safety measure such as a fuse should be implemented when use of the IC in a special mode where the absolute maximum ratings may be exceeded is anticipated.

2) GND potential

Ensure a minimum GND pin potential in all operating conditions. In addition, ensure that no pins other than the GND pin carry a voltage lower than or equal to the GND pin, including during actual transient phenomena.

Thermal design

Use a thermal design that allows for a sufficient margin in light of the power dissipation (Pd) in actual operating conditions.

4) Inter-pin shorts and mounting errors

Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may result in damage to the IC. Shorts between output pins or between output pins and the power supply and GND pin caused by the presence of a foreign object may result in damage to the IC.

5) Operation in a strong electromagnetic field

Use caution when using the IC in the presence of a strong electromagnetic field as doing so may cause the IC to malfunction.

6) Thermal shutdown circuit (TSD circuit)

This IC incorporates a built-in thermal shutdown circuit (TSD circuit). The TSD circuit is designed only to shut the IC off to prevent runaway thermal operation. Do not continue to use the IC after operating this circuit or use the IC in an environment where the operation of the thermal shutdown circuit is assumed.

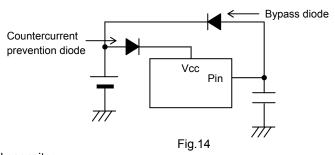
7) Testing on application boards

When testing the IC on an application board, connecting a capacitor to a pin with low impedance subjects the IC to stress. Always discharge capacitors after each process or step. Ground the IC during assembly steps as an antistatic measure, and use similar caution when transporting or storing the IC. Always turn the IC's power supply off before connecting it to or removing it from a jig or fixture during the inspection process.

8) Common impedance

Power supply and ground wiring should reflect consideration of the need to lower common impedance and minimize ripple as much as possible (by making wiring as short and thick as possible or rejecting ripple by incorporating inductance and capacitance).

9) Applications with modes that reverse VCC and pin potentials may cause damage to internal IC circuits. For example, such damage might occur when VCC is shorted with the GND pin while an external capacitor is charged. It is recommended to insert a diode for preventing back current flow in series with VCC or bypass diodes between VCC and each pin.



10) Timing resistor and capacitor

Timing resistor (capacitor) connected between RT (CT) and GND, has to be placed near RT (CT) terminal 3pin (4pin). And pattern has to be short enough.

- 11) The Dead time input voltage has to be set more than 1.1V. Also, the resistance between DTC and VREF is used more than $30k\Omega$ to work OCP function reliably.
- 12) The energy on DTC1(8pin)and DTC2(9pin)is discharged when CTL1(12pin)and CTL2(13pin)are OFF, respectively, or VCC(14pin)is OFF (UVLO activation). However, it is considerable to occur overshoot when CTL and VCC are turned on with remaining more than 1V on the DTC.

13) If Gate capacitance of P-channel MOSFET or resistance placed on

Gate is large, and the time from beginning of Gate switching to the end of Drain's (tsw), is long, it may not start up due to the OCP malfunction. To avoid it, select MOSFET or adjust resistance as tsw becomes less than 270nsec.

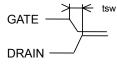


Fig.15

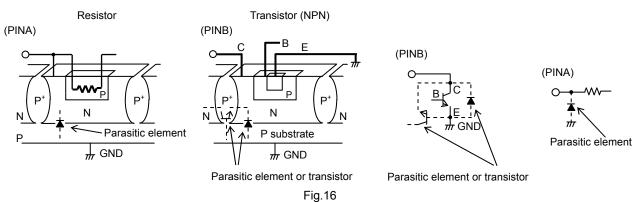
14) IC pin input

This monolithic IC contains P+ isolation and PCB layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements. For example, when a resistor and transistor are connected to pins as shown in following chart,

Othe P/N junction functions as a parasitic diode when GND > (Pin A) for the resistor or GND > (Pin B) for the transistor (NPN).

OSimilarly, when GND > (Pin B) for the transistor (NPN), the parasitic diode described above combines with the N layer of other adjacent elements to operate as a parasitic NPN transistor.

The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltages lower than the GND (PCB) voltage to input and output pins.



●Thermal Derating Curve

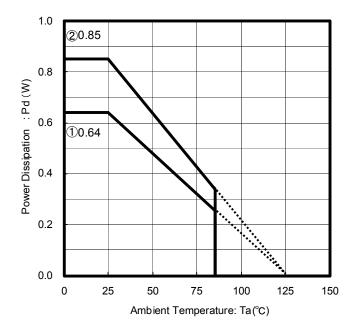
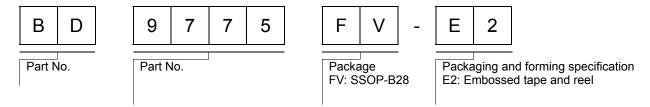


Fig.17

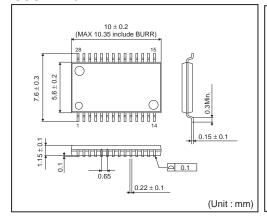
①With no heat sink

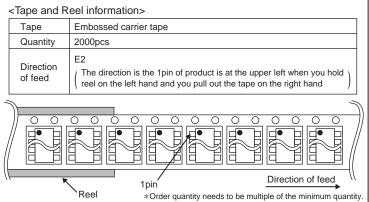
②Copper laminate area 70 mm × 70mm

Ordering part number



SSOP-B28





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